

PBSS5350D

50 V, 3 A PNP low VCEsat (BISS) transistor Rev. 6 — 28 June 2011

Product data sheet

Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350D

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High current capability
- High efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Supply line switching circuits
- Battery management applications
- DC-to-DC conversion

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _C	collector current		-	-	-3	Α
I _{CM}	peak collector current		-	-	-5	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = -2 \text{ A}; I_B = -200 \text{ mA}; \text{ pulsed};$ $t_p \le 300 \mu\text{s}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	120	150	mΩ



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector	D. D. D.	4.0.5.0
2	С	collector	<u> </u>	1, 2, 5, 6
3	В	base		3 —
4	Е	emitter	1 12 13	
5	С	collector	SOT457 (TSOP6)	4 sym030
6	С	collector		4,

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5350D	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5350D	53

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-60	V
V_{CEO}	collector-emitter voltage	open base		-	-50	V
V_{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-3	Α
I _{CM}	peak collector current			-	-5	Α
I _{BM}	peak base current			-	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	600	mW
			[2]	-	750	mW
			[3]	-	1200	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for collector 1 cm².

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	-	208	K/W
from junction to ambient		[2]	-	-	160	K/W	
	pulsed; $t_p \le 50$ ms; $\delta \le 0.5$.; in free air	[2]	-	-	100	K/W	

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

^[3] Device mounted on an FR4 4-layer PCB.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

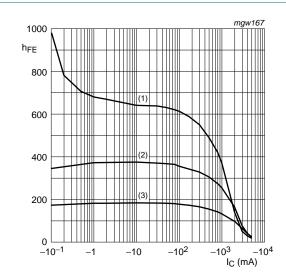
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7. Characteristics

Table 7. Characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = -50 V; I_E = 0 A; T_{amb} = 25 °C	-	-	-100	nΑ
	current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE} DC current gain	DC current gain	V_{CE} = -2 V; I_{C} = -500 mA; T_{amb} = 25 °C	200	-	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	200	-	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -2 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	100	-	-	
OLSai	collector-emitter	I_C = -500 mA; I_B = -50 mA; T_{amb} = 25 °C	-	-	-100	mV
	saturation voltage	$I_C = -1 \text{ A}; I_B = -50 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	-180	mV
		$I_C = -2 \text{ A}$; $I_B = -200 \text{ mA}$; pulsed;	-	-	-300	mV
R _{CEsat}	collector-emitter saturation resistance	t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	120	150	mΩ
V_{BEsat}	base-emitter saturation voltage		-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	-	-1.1	V
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	-	40	pF

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 $V_{CE} = -2 V$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55$ °C

Fig 1. DC current gain as a function of collector current; typical values

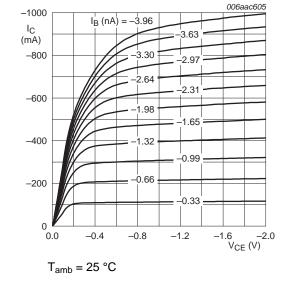


Fig 2. Collector current as a function of collector-emitter voltage; typical values

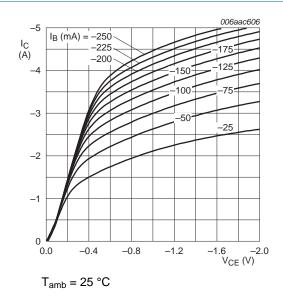
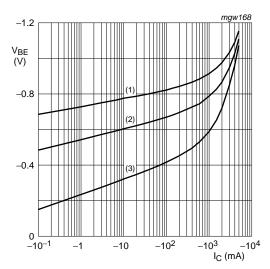


Fig 3. Collector current as a function of collector-emitter voltage; typical values



 $V_{CE} = -2 V$

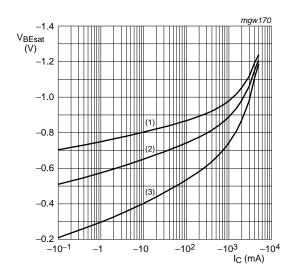
(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 4. Base-emitter voltage as a function of collector current; typical values

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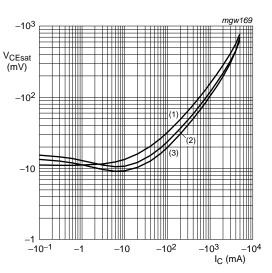


$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55$$
 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 5. Base-emitter saturation voltage as a function of collector current; typical values



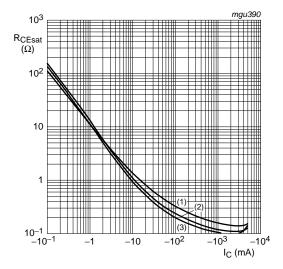
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(2)
$$T_{amb} = 25$$
 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation resistance as a function of collector current; typical values

8. Package outline

Plastic surface-mounted package (TSOP6); 6 leads SOT457 B Company to the property of the pr

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	bp	С	D	E	е	HE	Lp	Q	v	w	у
mm	1.1 0.9	0.1 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

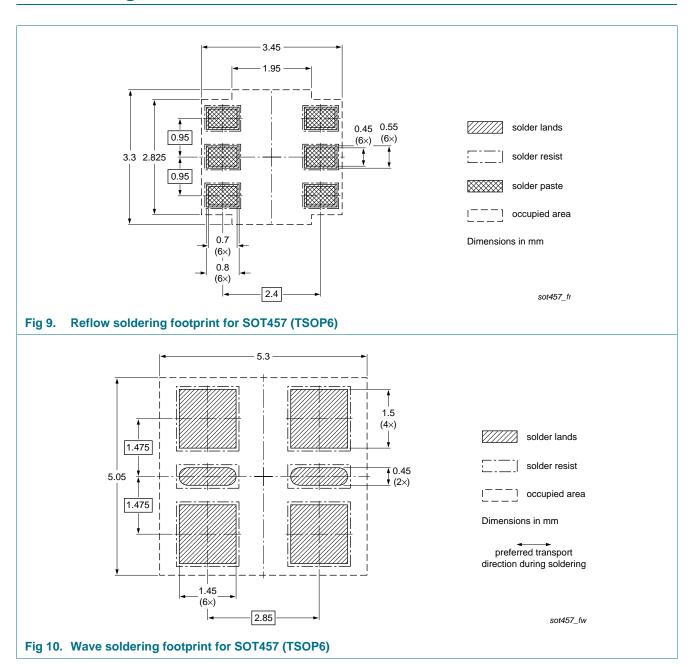
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT457			SC-74		-05-11-07- 06-03-16

Fig 8. Package outline SOT457 (TSOP6)

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9. Soldering



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10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5350D v.6	20110628	Product data sheet	-	PBSS5350D v.5
Modifications:	 5 "Limiting values" 	: P _{tot} conditions updated.		
PBSS5350D v.5	20110323	Product data sheet	-	PBSS5350D v.4
PBSS5350D v.4	20011113	Product specification	-	PBSS5350D v.3
PBSS5350D v.3	20010713	Product specification	-	PBSS5350D v.2
PBSS5350D v.2	20010126	Product specification	-	PBSS5350D v.1
PBSS5350D v.1	20000308	Product specification	-	-

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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